

# Thyristor Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

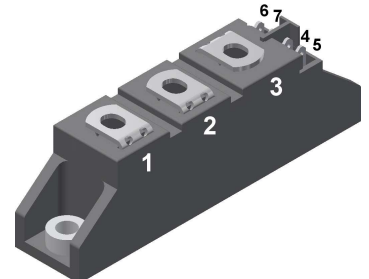
$$I_{TAV} = 18 \text{ A}$$

$$V_T = 1.57 \text{ V}$$

Phase leg

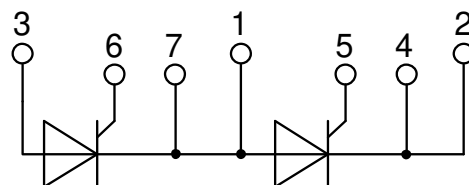
Part number

**MCC19-12io1B**



Backside: isolated

 E72873



## Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al<sub>2</sub>O<sub>3</sub>-ceramic

## Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

## Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

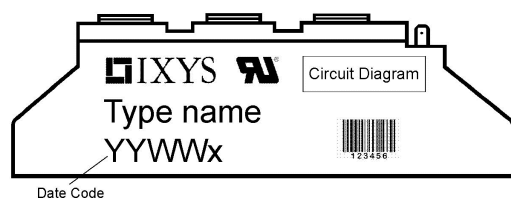
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| Thyristor      |                                                      |                                                                                                                                                                        |                                | Ratings |      |      |                  |
|----------------|------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------|---------|------|------|------------------|
| Symbol         | Definition                                           | Conditions                                                                                                                                                             |                                | min.    | typ. | max. | Unit             |
| $V_{RSM/DSM}$  | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}\text{C}$                                                                                                                                          |                                |         |      | 1300 | V                |
| $V_{RRM/DRM}$  | max. repetitive reverse/forward blocking voltage     | $T_{VJ} = 25^{\circ}\text{C}$                                                                                                                                          |                                |         |      | 1200 | V                |
| $I_{R/D}$      | reverse current, drain current                       | $V_{R/D} = 1200\text{ V}$                                                                                                                                              | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 100  | $\mu\text{A}$    |
|                |                                                      | $V_{R/D} = 1200\text{ V}$                                                                                                                                              | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 3    | mA               |
| $V_T$          | forward voltage drop                                 | $I_T = 40\text{ A}$                                                                                                                                                    | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 1.56 | V                |
|                |                                                      | $I_T = 80\text{ A}$                                                                                                                                                    |                                |         |      | 2.05 | V                |
|                |                                                      | $I_T = 40\text{ A}$                                                                                                                                                    | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 1.57 | V                |
|                |                                                      | $I_T = 80\text{ A}$                                                                                                                                                    |                                |         |      | 2.29 | V                |
| $I_{TAV}$      | average forward current                              | $T_C = 85^{\circ}\text{C}$                                                                                                                                             | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 18   | A                |
| $I_{T(RMS)}$   | RMS forward current                                  | 180° sine                                                                                                                                                              |                                |         |      | 28   | A                |
| $V_{T0}$       | threshold voltage                                    | for power loss calculation only                                                                                                                                        | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 0.85 | V                |
| $r_T$          | slope resistance                                     |                                                                                                                                                                        |                                |         |      | 18   | m $\Omega$       |
| $R_{thJC}$     | thermal resistance junction to case                  |                                                                                                                                                                        |                                |         |      | 1.3  | K/W              |
| $R_{thCH}$     | thermal resistance case to heatsink                  |                                                                                                                                                                        |                                |         | 0.2  |      | K/W              |
| $P_{tot}$      | total power dissipation                              |                                                                                                                                                                        | $T_C = 25^{\circ}\text{C}$     |         |      | 77   | W                |
| $I_{TSM}$      | max. forward surge current                           | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$                                                                                                                       | $T_{VJ} = 45^{\circ}\text{C}$  |         |      | 400  | A                |
|                |                                                      | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$                                                                                                                      | $V_R = 0\text{ V}$             |         |      | 430  | A                |
|                |                                                      | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$                                                                                                                       | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 340  | A                |
|                |                                                      | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$                                                                                                                      | $V_R = 0\text{ V}$             |         |      | 365  | A                |
| $I^2t$         | value for fusing                                     | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$                                                                                                                       | $T_{VJ} = 45^{\circ}\text{C}$  |         |      | 800  | A <sup>2</sup> s |
|                |                                                      | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$                                                                                                                      | $V_R = 0\text{ V}$             |         |      | 770  | A <sup>2</sup> s |
|                |                                                      | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$                                                                                                                       | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 580  | A <sup>2</sup> s |
|                |                                                      | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$                                                                                                                      | $V_R = 0\text{ V}$             |         |      | 555  | A <sup>2</sup> s |
| $C_J$          | junction capacitance                                 | $V_R = 400\text{ V}$ $f = 1\text{ MHz}$                                                                                                                                | $T_{VJ} = 25^{\circ}\text{C}$  |         | 22   |      | pF               |
| $P_{GM}$       | max. gate power dissipation                          | $t_p = 30\text{ }\mu\text{s}$                                                                                                                                          | $T_C = 125^{\circ}\text{C}$    |         |      | 10   | W                |
|                |                                                      | $t_p = 300\text{ }\mu\text{s}$                                                                                                                                         |                                |         |      | 5    | W                |
| $P_{GAV}$      | average gate power dissipation                       |                                                                                                                                                                        |                                |         |      | 0.5  | W                |
| $(di/dt)_{cr}$ | critical rate of rise of current                     | $T_{VJ} = 125^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 75\text{ A}$                                                                                       |                                |         |      | 150  | A/ $\mu\text{s}$ |
|                |                                                      | $t_p = 200\text{ }\mu\text{s}; di_G/dt = 0.45\text{ A}/\mu\text{s};$<br>$I_G = 0.45\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 18\text{ A}$                 |                                |         |      | 500  | A/ $\mu\text{s}$ |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage                     | $V = \frac{2}{3} V_{DRM}$<br>$R_{GK} = \infty$ ; method 1 (linear voltage rise)                                                                                        | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 1000 | V/ $\mu\text{s}$ |
| $V_{GT}$       | gate trigger voltage                                 | $V_D = 6\text{ V}$                                                                                                                                                     | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 1.5  | V                |
|                |                                                      |                                                                                                                                                                        | $T_{VJ} = -40^{\circ}\text{C}$ |         |      | 1.6  | V                |
| $I_{GT}$       | gate trigger current                                 | $V_D = 6\text{ V}$                                                                                                                                                     | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 100  | mA               |
|                |                                                      |                                                                                                                                                                        | $T_{VJ} = -40^{\circ}\text{C}$ |         |      | 200  | mA               |
| $V_{GD}$       | gate non-trigger voltage                             | $V_D = \frac{2}{3} V_{DRM}$                                                                                                                                            | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 0.2  | V                |
| $I_{GD}$       | gate non-trigger current                             |                                                                                                                                                                        |                                |         |      | 5    | mA               |
| $I_L$          | latching current                                     | $t_p = 10\text{ }\mu\text{s}$                                                                                                                                          | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 450  | mA               |
|                |                                                      | $I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$                                                                                                             |                                |         |      |      |                  |
| $I_H$          | holding current                                      | $V_D = 6\text{ V}$ $R_{GK} = \infty$                                                                                                                                   | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 200  | mA               |
| $t_{gd}$       | gate controlled delay time                           | $V_D = \frac{1}{2} V_{DRM}$                                                                                                                                            | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 2    | $\mu\text{s}$    |
|                |                                                      | $I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$                                                                                                             |                                |         |      |      |                  |
| $t_q$          | turn-off time                                        | $V_R = 100\text{ V}; I_T = 20\text{ A}; V = \frac{2}{3} V_{DRM}$<br>$di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 20\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$ | $T_{VJ} = 100^{\circ}\text{C}$ |         | 150  |      | $\mu\text{s}$    |

| Package TO-240AA     |                                                              |                      |                                         | Ratings |      |      |      |
|----------------------|--------------------------------------------------------------|----------------------|-----------------------------------------|---------|------|------|------|
| Symbol               | Definition                                                   | Conditions           |                                         | min.    | typ. | max. | Unit |
| I <sub>RMS</sub>     | RMS current                                                  | per terminal         |                                         |         |      | 200  | A    |
| T <sub>VJ</sub>      | virtual junction temperature                                 |                      |                                         | -40     |      | 125  | °C   |
| T <sub>op</sub>      | operation temperature                                        |                      |                                         | -40     |      | 100  | °C   |
| T <sub>stg</sub>     | storage temperature                                          |                      |                                         | -40     |      | 125  | °C   |
| Weight               |                                                              |                      |                                         |         | 81   |      | g    |
| M <sub>D</sub>       | mounting torque                                              |                      |                                         | 2.5     |      | 4    | Nm   |
| M <sub>T</sub>       | terminal torque                                              |                      |                                         | 2.5     |      | 4    | Nm   |
| d <sub>Spp/App</sub> | creepage distance on surface   striking distance through air | terminal to terminal | 13.0                                    | 9.7     |      |      | mm   |
| d <sub>Spb/Apb</sub> |                                                              | terminal to backside | 16.0                                    | 16.0    |      |      | mm   |
| V <sub>ISOL</sub>    | isolation voltage                                            | t = 1 second         | 50/60 Hz, RMS; I <sub>ISOL</sub> ≤ 1 mA |         | 4800 |      | V    |
|                      |                                                              | t = 1 minute         |                                         |         | 4000 |      | V    |



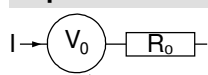
| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | MCC19-12io1B    | MCC19-12io1B       | Box           | 36       | 452831   |

| Similar Part  | Package     | Voltage class |
|---------------|-------------|---------------|
| MCMA25P1200TA | TO-240AA-1B | 1200          |
| MCMA35P1200TA | TO-240AA-1B | 1200          |

### Equivalent Circuits for Simulation

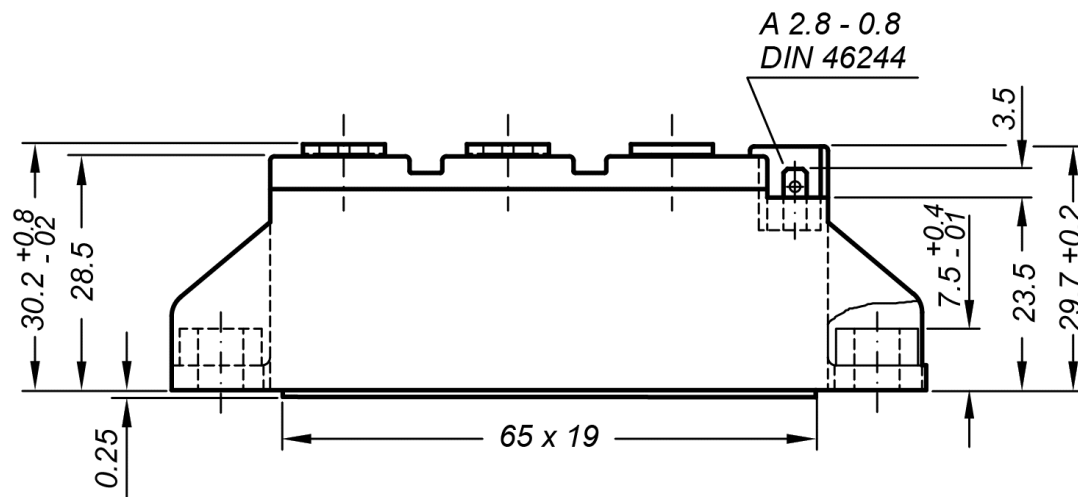
\* on die level

$T_{VJ} = 125^{\circ}\text{C}$

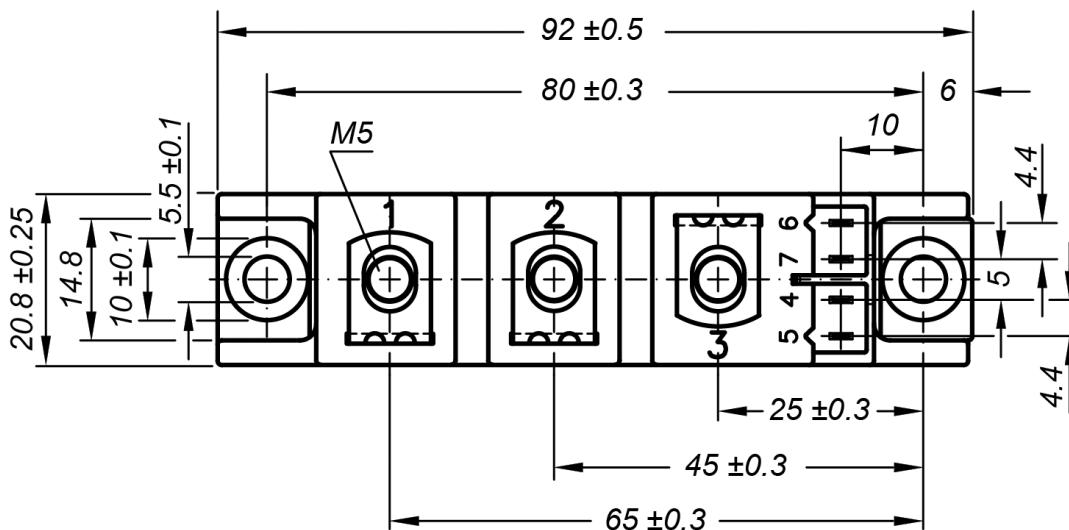
|                                                                                     |                    |                  |    |
|-------------------------------------------------------------------------------------|--------------------|------------------|----|
|  |                    | <b>Thyristor</b> |    |
| $V_{0\ max}$                                                                        | threshold voltage  | 0.85             | V  |
| $R_{0\ max}$                                                                        | slope resistance * | 16.8             | mΩ |



**Outlines TO-240AA**



General tolerance: DIN ISO 2768 class „C“



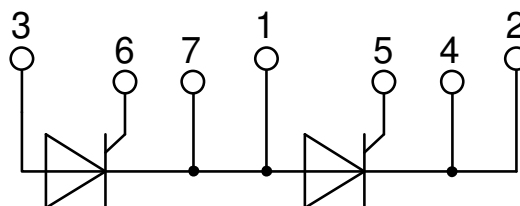
**Optional accessories for modules**

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

Type ZY 200L (L = Left for pin pair 4/5)

Type ZY 200R (R = Right for pin pair 6/7)

UL 758, style 3751



## Thyristor

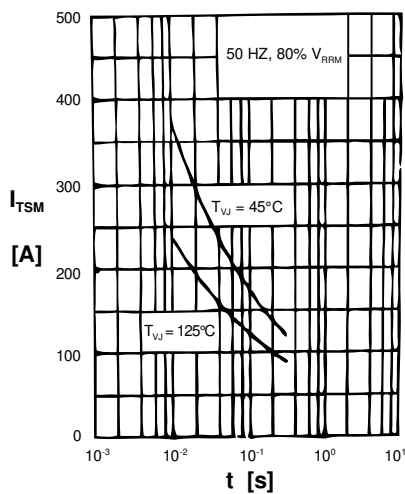


Fig. 1 Surge overload current  
 $I_{TSM}$ : Crest value,  $t$ : duration

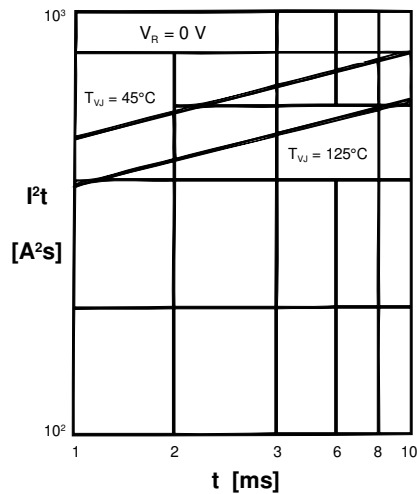


Fig. 2  $I^2t$  versus time (1-10 ms)

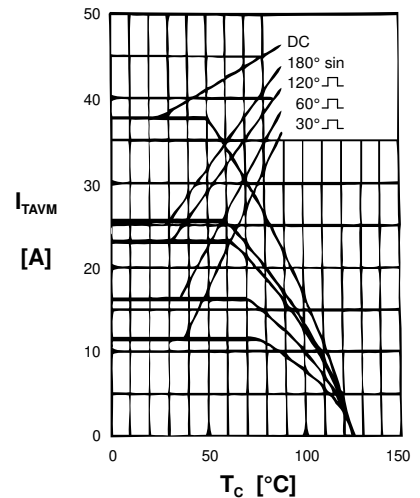


Fig. 3 Max. forward current  
 at case temperature

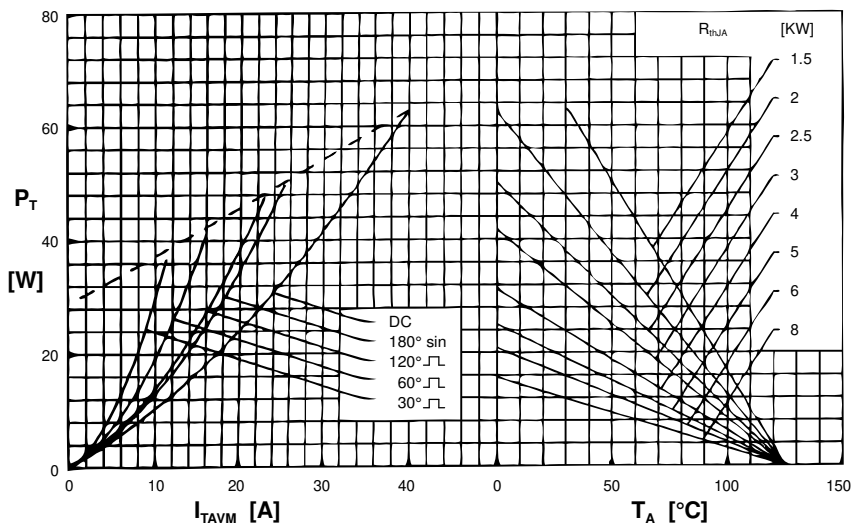


Fig. 4 Power dissipation versus onstate current & ambient temp. (per thyristor)

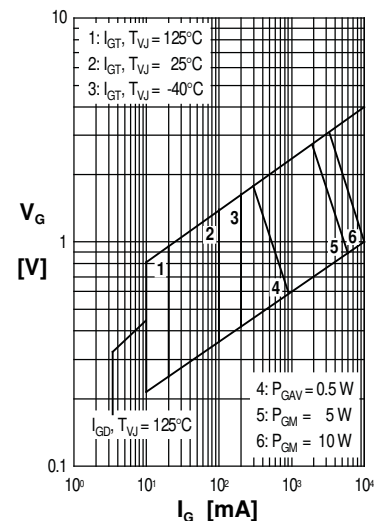


Fig. 5 Gate trigger charact.

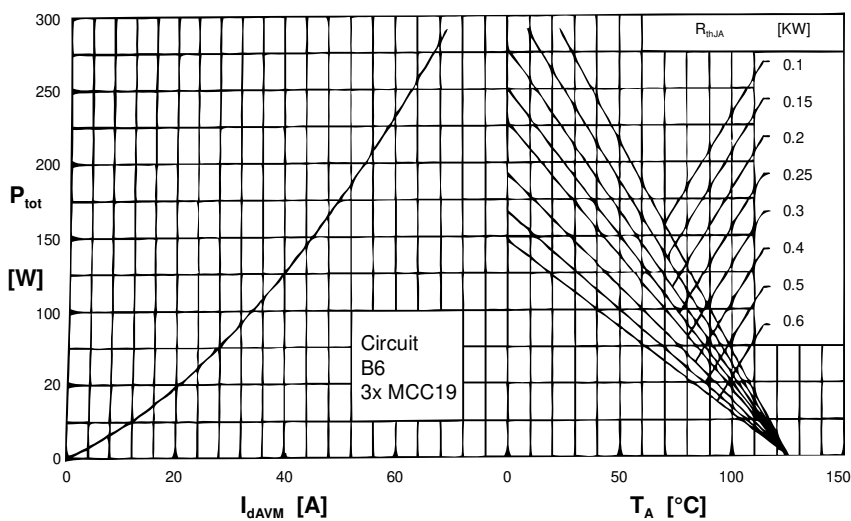


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct  
 output current and ambient temperature

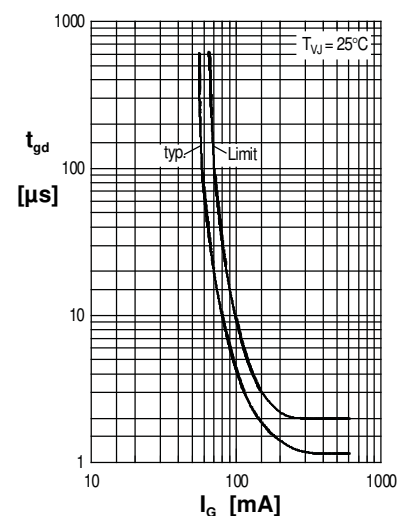


Fig. 7 Gate trigger delay time

## Thyristor

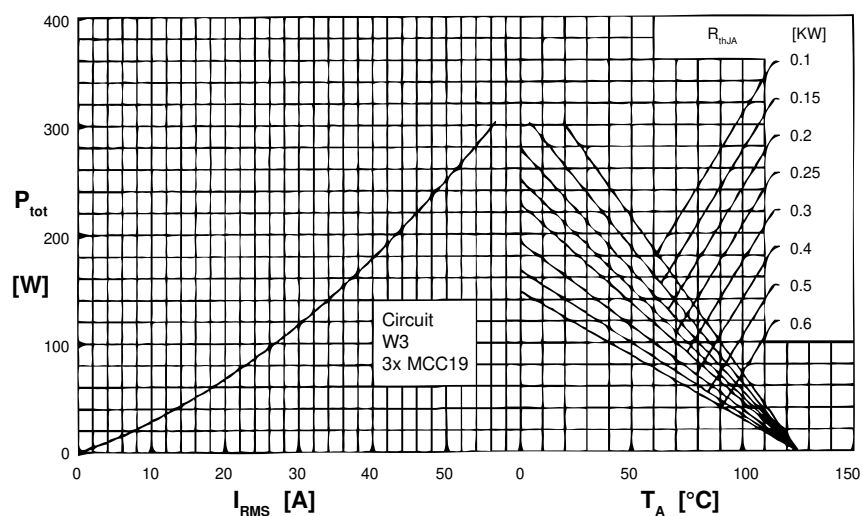


Fig. 8 Three phase AC-controller: Power dissipation vs. RMS output current and ambient temperature

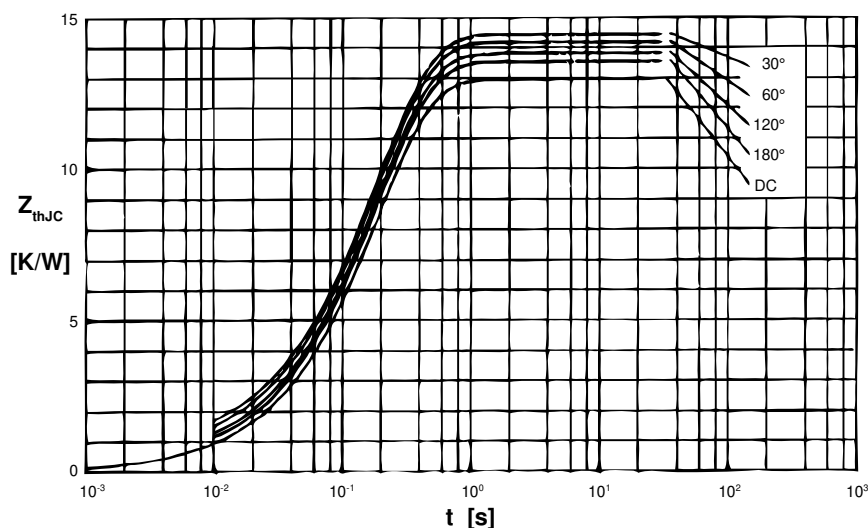


Fig. 9 Transient thermal impedance junction to case (per thyristor)

$R_{thJC}$  for various conduction angles  $d$ :

| $d$  | $R_{thJC}$ [K/W] |
|------|------------------|
| DC   | 1.30             |
| 180° | 1.35             |
| 120° | 1.39             |
| 60°  | 1.42             |
| 30°  | 1.45             |

Constants for  $Z_{thJC}$  calculation:

| $i$ | $R_{thi}$ [K/W] | $t_i$ [s] |
|-----|-----------------|-----------|
| 1   | 0.018           | 0.0033    |
| 2   | 0.041           | 0.0216    |
| 3   | 1.241           | 0.1910    |

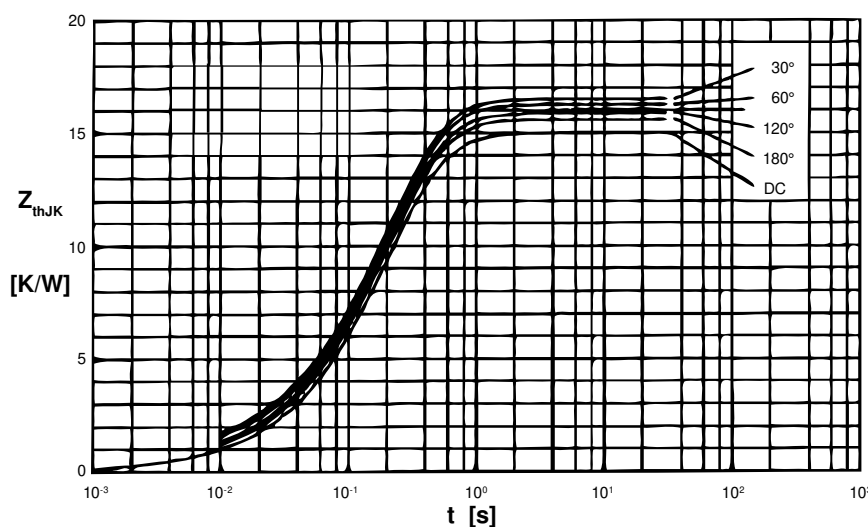


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor)

$R_{thJK}$  for various conduction angles  $d$ :

| $d$  | $R_{thJK}$ [K/W] |
|------|------------------|
| DC   | 1.50             |
| 180° | 1.55             |
| 120° | 1.59             |
| 60°  | 1.62             |
| 30°  | 1.65             |

Constants for  $Z_{thJK}$  calculation:

| $i$ | $R_{thi}$ [K/W] | $t_i$ [s] |
|-----|-----------------|-----------|
| 1   | 0.018           | 0.0033    |
| 2   | 0.041           | 0.0216    |
| 3   | 1.241           | 0.1910    |
| 4   | 0.200           | 0.4600    |